



## Components and Instrumentation

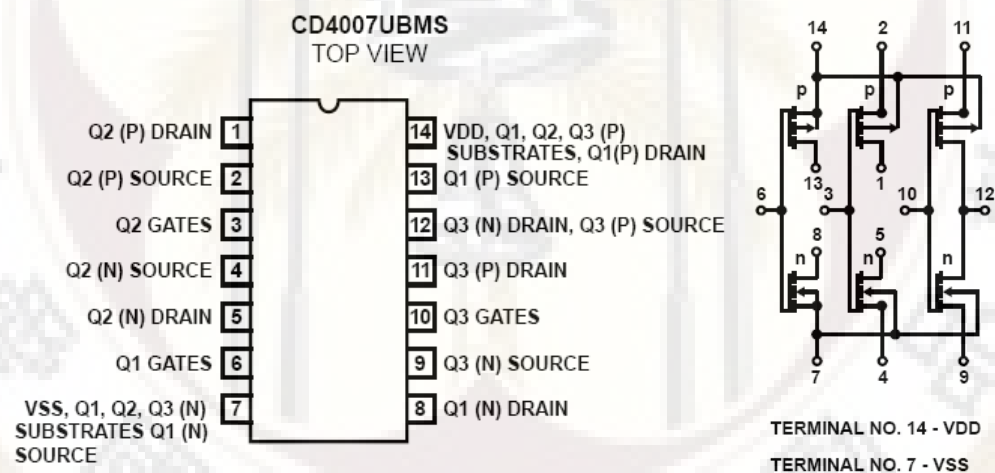
Instrument	Quantity	Components	Quantity
Oscilloscope	1	CD 4007	3
Multi-meter	1	VR (可變電阻) (1 k $\Omega$ )	1
Power supplier	1	10 k $\Omega$	1
Function Gen.	1	1 k $\Omega$	1
		18 k $\Omega$	2

## Instrument confirmation

Before you proceed to any part of the experiment, please remember to do the **Instrument Examinations** to the instruments before performing any experiment. The examining procedures are shown in experiment 1.

## Lab Work

### 1. CD4007 – PINOUT



※**Note:** Always supply voltage  $-V_{SS} = -8V$  in **pin 7** and  $V_{DD} = +8V$  in **pin 14** for every chip of CD4007. The experimental results will be unreasonable if the above notice has not been followed.

- (1) Employ CD4007 Chip #A to implement  $(Q_5, Q_7, Q_8)$ , Chip #B to implement  $(Q_1, Q_2)$ , and Chip #C for  $(Q_3, Q_4, Q_6)$
- (2) Supply voltage  $-V_{SS} = -8V$  (pin7) and  $V_{DD} = +8V$  (pin 14) for CD4007 chips.

- (1) The condition of entering saturation region of NMOS:  $V_{GD} \leq V_T$  (1.8V).
- (2) The condition of entering saturation region of PMOS:  $V_{GD} \geq V_T$  (-1.8V).
- (3) Supply voltage  $-V_{SS} = -8V$  and  $V_{DD} = +8V$  to the circuit.
- (4) Use digital multi-meter to confirm whether all of the MOS components are able to enter saturation region as adjusting VR 1 k $\Omega$ .
- (5) If it is so, go to step 6, else go to next step.

- (1) DC Analysis of the current mirror ( $Q_5, Q_7, Q_8$ )
  - a. In Fig. 3, adjust VR ( $R_2$ ) 10 k $\Omega$  and check whether ( $Q_5, Q_7, Q_8$ ) are all able to enter saturation region, that is,  $V_{GD5,7,8} \geq V_T (-1.8\text{V})$ . If one of them is not so, change the chip of CD4007 #A and recheck again.
  - b. Use multi-meter (三用電錶) to measure  $V_{GD5}, V_{GD7}, V_{GD8}$
  - c. Record  $V_{GD5} =$             V,  $V_{GD7} =$             V,  $V_{GD8} =$             V.

## Analysis

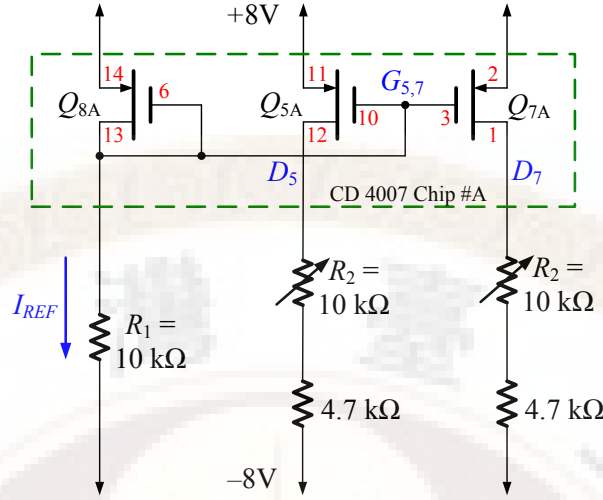


Fig. 3 DC Analysis of the current mirror ( $Q_5$ ,  $Q_7$ ,  $Q_8$ )

$\because V_{SG8} = V_{SG5} = V_{SG7}$ , If  $Q_8 = Q_5 = Q_7$ , then  $I_{D8} = I_{D5} = I_{D7} = I_{REF}$ .

$V_{G5} = V_{G7} = V_{G8} = V_{D8} = -8V + I_{REF} \times R_1$ ,

$V_{D5} = V_{D7} = -8V + I_{REF} \times (R_2 + 4.7k\Omega)$ ,

$\rightarrow V_{GD5} = V_{G5} - V_{D5} = I_{REF} \times [(R_1 - R_2) + 4.7k\Omega] \geq V_T (-1.8V)$ .....(1)

If eq.(1) can not be true, that means  $I_{REF}$  is not big enough or  $I_{REF}$  is equal 0, that is, the current mirror does not work.

### (2) DC Analysis of the differential pair ( $Q_1, Q_2$ )

- In Fig. 4, adjust VR ( $R_2$ ) 10 kΩ and check whether ( $Q_1$ ,  $Q_2$ ) are both able to enter saturation region, that is,  $V_{GD1,2} \geq V_T (-1.8V)$ . If one of them is not so, change the chip of CD4007 #B and recheck again.
- Use multi-meter (三用電錶) to measure  $V_{GD1}$ ,  $V_{GD2}$ .
- Record  $V_{GD1} = \underline{\hspace{1cm}}$  V,  $V_{GD2} = \underline{\hspace{1cm}}$  V.

## Analysis

$\because V_{SG8} = V_{SG5}$  and  $V_{SG1} = V_{SG2}$ , If  $Q_8 = Q_5$  and  $Q_1 = Q_2$ ,

then  $I_{D8} = I_{D5} = I_{REF}$ ,  $I_{D1} = I_{D2} = \frac{I_{REF}}{2}$ ,

$V_{G1} = V_{G2} = 0V$ ,  $V_{D1} = V_{D2} = -8V + I_{D1} \times R_2$ ,

$\rightarrow V_{GD1} = V_{G1} - V_{D1} = 8 - I_{D1} \times R_2 = 8 - \frac{I_{REF}}{2} \times R_2 \geq V_T (-1.8V)$ .....(2)

If eq.(2) cannot be true, that means  $I_{D1} \times R_2$  can not be small enough.

It is possibly that  $R_2$  is too big or ( $Q_1, Q_2$ ) mismatch, try to change smaller  $R_2$  or change a new chip#B.

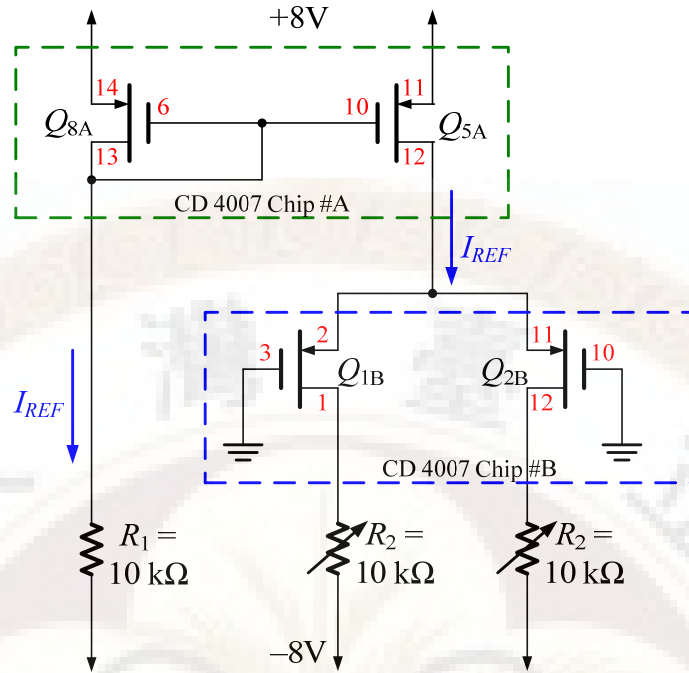


Fig. 4 DC Analysis of the differential pair ( $Q_1$ ,  $Q_2$ )

(3) DC Analysis of the active load ( $Q_3$ ,  $Q_4$ )

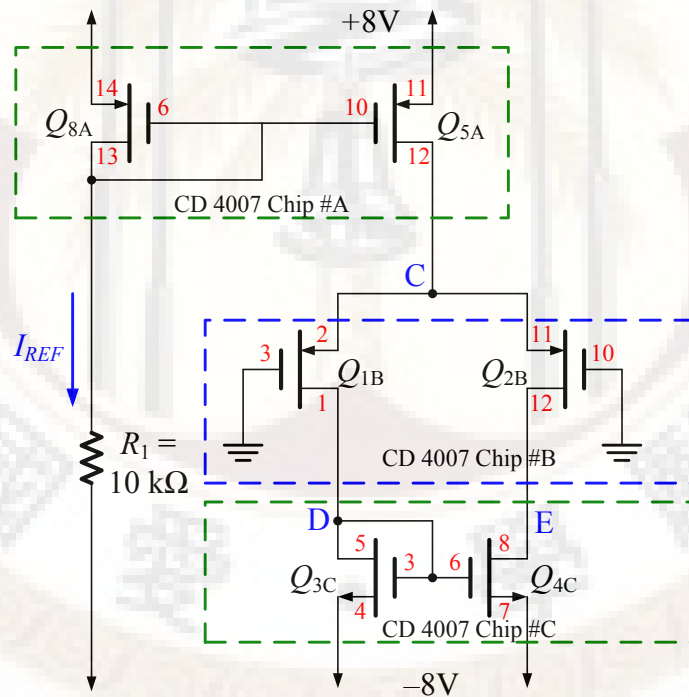


Fig. 5 DC Analysis of the active load ( $Q_3$ ,  $Q_4$ )

- a. In Fig. 5, Use multi-meter (三用電錶) to check whether ( $Q_3$ ,  $Q_4$ ) are both able to enter saturation region, that is,  $V_{GD3,4} \geq V_T (-1.8V)$ . If one of them is not so, change the chip of CD4007 #C and recheck again.

- b. Record  $V_{GD1} = \underline{\hspace{1cm}}$  V,  $V_{GD2} = \underline{\hspace{1cm}}$  V,  $V_{GD3} = \underline{\hspace{1cm}}$  V,  $V_{GD4} = \underline{\hspace{1cm}}$  V.  
c. Record  $V_C = \underline{\hspace{1cm}}$  V,  $V_D = \underline{\hspace{1cm}}$  V,  $V_E = \underline{\hspace{1cm}}$  V.

### Analysis

$\because V_{SG8} = V_{SG5}$  and  $V_{SG1} = V_{SG2}$ , If  $Q_8 = Q_5$ ,  $Q_1 = Q_2$ , and  $Q_3 = Q_4$ ,

then  $I_{D8} = I_{D5} = I_{REF}$ ,  $I_{D1} = I_{D2} = I_{D3} = I_{D4} = \frac{I_{REF}}{2}$ ,

$V_{G3} = V_{D3} \rightarrow V_{GD3} = 0 \rightarrow Q_3$  will always be saturated.

$V_{G4} = V_{G3} = V_{D1} = -8V + I_{D1} \times R_{DS3}$ ,  $V_{D4} = -8V + I_{D1} \times R_{DS4}$ ,

$\rightarrow V_{GD4} = V_{D1} - V_{D4} \approx 0 \leq V_T (1.8V)$ .....(3)

$$R_{DS4} = \left( \frac{\Delta i_{D4}}{\Delta v_{DS4}} \right)^{-1} = \left( \frac{\partial}{\partial v_{DS4}} \left\{ k'_n \left( \frac{W}{L} \right) \left[ (v_{GS4} - V_T) v_{DS4} - \frac{1}{2} v_{DS4}^2 \right] \right\} \right)^{-1}$$

$$\rightarrow R_{DS4} = \left\{ k'_n \left( \frac{W}{L} \right) \left[ (v_{GS4} - V_T) - \frac{1}{2} v_{DS4} \right] \right\}^{-1}$$

If eq. (3) can not be true, that means there is something wrong with  $Q_{4C}$ .

Try to change a new chip#C.

### 5. DC Analysis of the Two-stage OP-Amp circuit

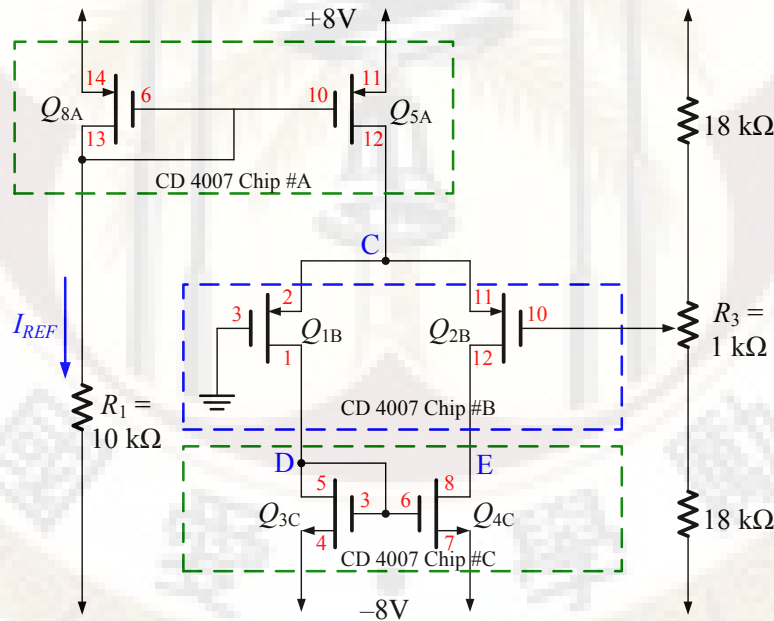


Fig. 6 DC Analysis of Two-stage OP-Amp circuit

- a. In Fig. 6, adjust VR ( $R_3$ ) 1 kΩ and use multi-meter to measure  $V_A$  and  $V_E$ , and check whether  $V_E$  is adjustable. If it not so, trouble shoot the circuit. Check whether there is any wrong layout in your breadboard and whether the VR ( $R_3$ ) is functional by multimeter.  
b. Referenced value of  $V_A$  is around (-0.25V, 0.25V),  $V_E$  is around (0.25V,

-7.5V). Record  $V_A = ( \quad \text{V}, \quad \text{V} )$  and  $V_E = ( \quad \text{V}, \quad \text{V} )$ .

## 6. Circuit implementation

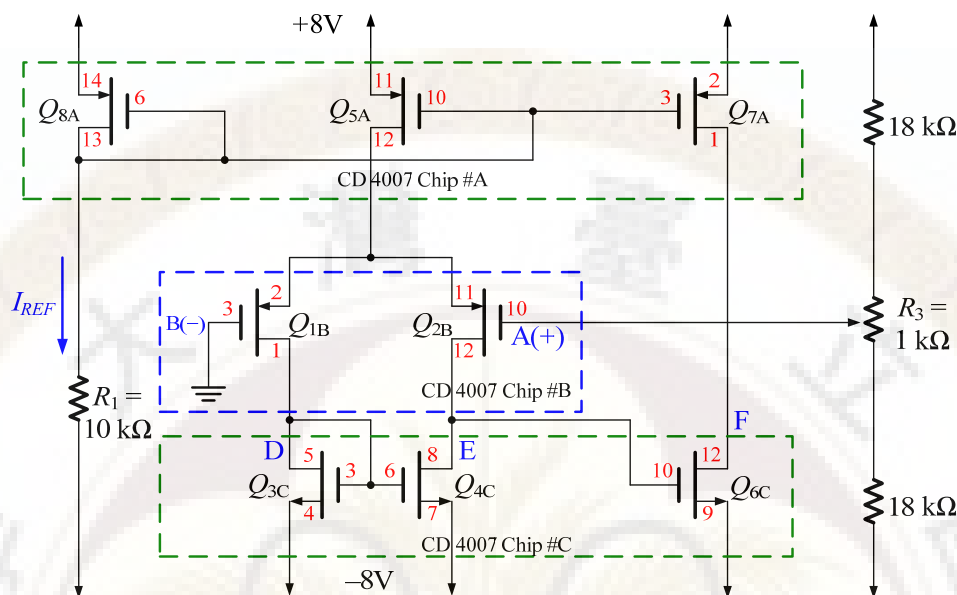


Fig. 2 DC Analysis of Two-stage OP-Amp circuit

- In Fig. 2, adjust VR ( $R_3$ ) 1 kΩ and use multi-meter to measure  $V_A$ ,  $V_D$ ,  $V_E$ .
- Referenced value of  $V_A$  is around (-0.25V, 0.25V),  $V_E$  is around (0.25V, -7.5V), and  $V_F$  is around (-7.5V, 7.5V)
- Adjust VR ( $R_3$ ), and record  $V_A$ ,  $V_E$ ,  $V_F$  in the following table.

$V_A$ (V)	$V_E$ (V)	$V_F$ (V)	$V_A$ (V)	$V_E$ (V)	$V_F$ (V)

*Homework #1:* Apply the measured data from the above table to the editing software such as EXCEL and MATLAB, and illustrate the *DC-sweep diagram* similar to Fig. 7 with marking the corresponding voltage. Try to calculate the *slope rate* of the diagram in the transition region.

7. If the remaining time is allowed to do Exp 4 right away, go directly to the next chapter. Strongly suggest that you perform Exp. 4 right after this experiment.
8. If it is not so, it will be rather time-wasting to restart all the procedures shown in the experiment as you perform Exp. 4 next week, which is mainly to make sure all the MOS components are able to enter saturation region.

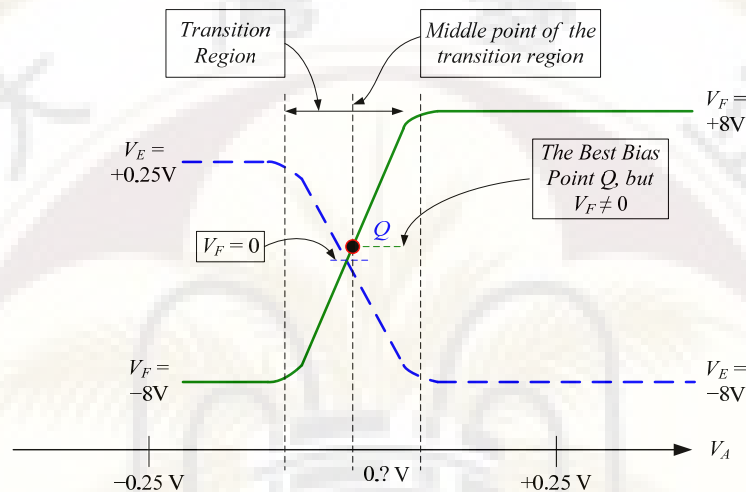


Fig. 7 DC-Sweep diagram

## Reference

1. A.S. Sedra and K.C. Smith, *Microelectronic Circuits*, 6th ed., Oxford University Press publishing, New York, August 2011.
2. A.S. Sedra and K.C. Smith, *Laboratory Manual for Microelectronic Circuits*, 3<sup>rd</sup> ed., Oxford University Press publishing, New York, 1997.